

### SANYO Semiconductors

## DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

# SFT1443 — General-Purpose Switching Device Applications

#### **Features**

- ON-resistance RDS(on)1=180m $\Omega$ (typ.)
- · 4V drive

- Input Capacitance Ciss=490pF(typ.)
- · Halogen free compliance

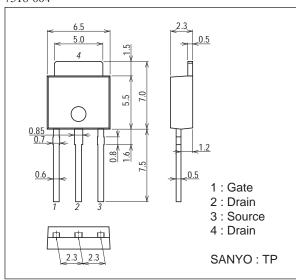
#### **Specifications**

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		100	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	ID		9	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	36	Α
Allowable Power Dissipation	D-		1	W
	PD	Tc=25°C	19	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

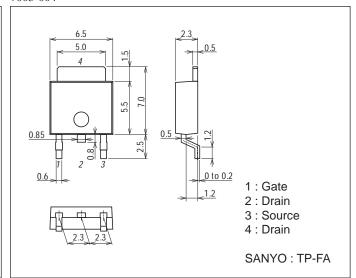
#### **Package Dimensions**

unit : mm (typ) 7518-004



#### **Package Dimensions**

unit : mm (typ) 7003-004



#### **Product & Package Information**

• Package : TP

• JEITA, JEDEC: SC-64, TO-251, SOT-553, DPAK

• Minimum Packing Quantity: 500 pcs./bag

Marking(TP, TP-FA)



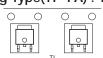
#### **Product & Package Information Electrical Connection**

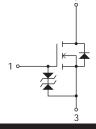
• Package : TP-FA

• JEITA, JEDEC: SC-63, TO-252, SOT-428, DPAK

• Minimum Packing Quantity: 700 pcs./reel

Packing Type(TP-FA): TL





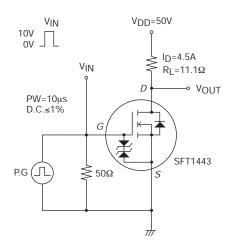
**SANYO Semiconductor Co., Ltd.** 

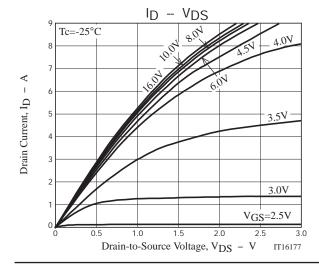
http://semicon.sanyo.com/en/network

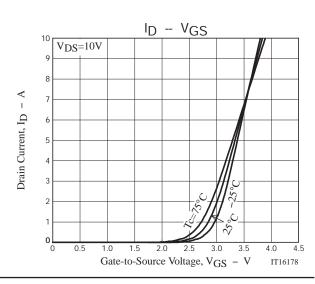
#### Electrical Characteristics at Ta=25°C

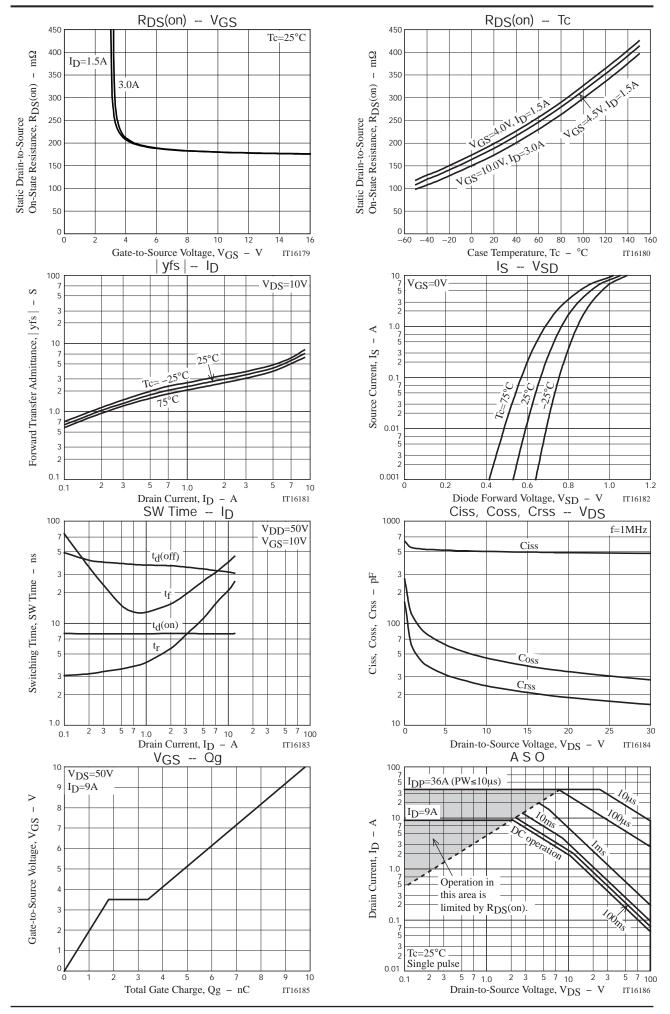
Parameter	Symbol	Conditions	Ratings			Linit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	100			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.5		2.6	V
Forward Transfer Admittance	yfs	VDS=10V, ID=4.5A		4		S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =3A, V <sub>GS</sub> =10V		180	225	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =1.5A, V <sub>G</sub> S=4.5V		195	275	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =1.5A, V <sub>G</sub> S=4V		205	290	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =20V, f=1MHz		490		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		34		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =20V, f=1MHz		19		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		8		ns
Rise Time	tr	See specified Test Circuit.		10		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		34		ns
Fall Time	tf	See specified Test Circuit.		24		ns
Total Gate Charge	Qg	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =9A		9.8		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =9A		1.8		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =9A		1.6		nC
Diode Forward Voltage	V <sub>SD</sub>	IS=9A, VGS=0V		1.03	1.2	V

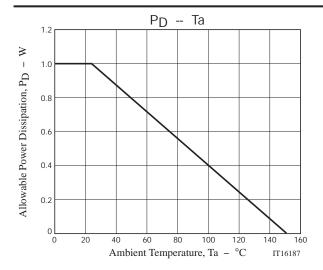
#### **Switching Time Test Circuit**

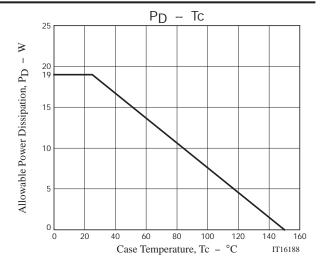












Note on usage: Since the SFT1443 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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